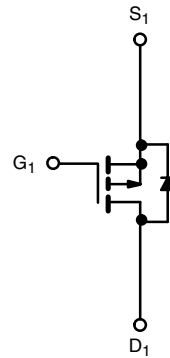
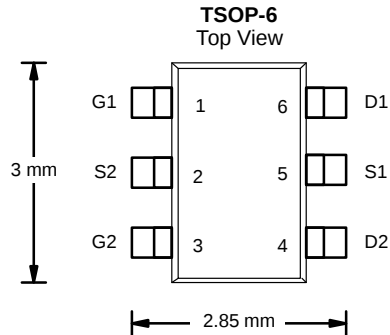


Dual P-Channel 60-V (D-S) MOSFET

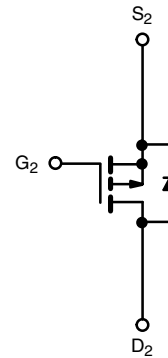
PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω) Typ.	I_D (A) ^d	Q_g (TYP.)
-60	0.070 at $V_{GS} = -10$ V	-4.5	10.1 nC
	0.085 at $V_{GS} = -4.5$ V	-4.0	

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- Trench Power MOSFET
- Compliant to RoHS Directive 2002/95/EC


RoHS
 COMPLIANT


P-Channel MOSFET



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	-60	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current ($T_J = 150$ °C)	$T_C = 25$ °C	I_D	-4.5	A
	$T_C = 70$ °C		-4.0	
	$T_A = 25$ °C		-3.5 ^{a,b}	
	$T_A = 70$ °C		-3.0 ^{a,b}	
Pulsed Drain Current ($t = 100$ μ s)		I_{DM}	-20	
Continuous Source-Drain Diode Current	$T_C = 25$ °C	I_S	-3.9	
	$T_A = 25$ °C		-2.1 ^{a,b}	
Avalanche Current		I_{AS}	-15	mJ
Single-Pulse Avalanche Energy		E_{AS}	11.25	
Maximum Power Dissipation	$T_C = 25$ °C	P_D	4.2	W
	$T_C = 70$ °C		2.7	
	$T_A = 25$ °C		2 ^{a,b}	
	$T_A = 70$ °C		1.3 ^{a,b}	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient ^a	$t \leq 5$ s	R_{thJA}	100	130	°C/W
Maximum junction-to-case (drain)	Steady state	R_{thJF}	60	75	

Notes

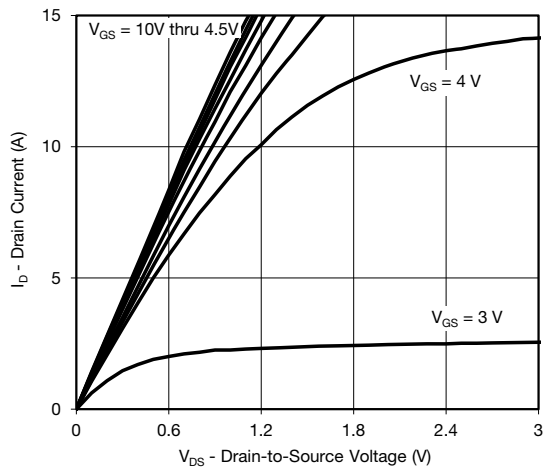
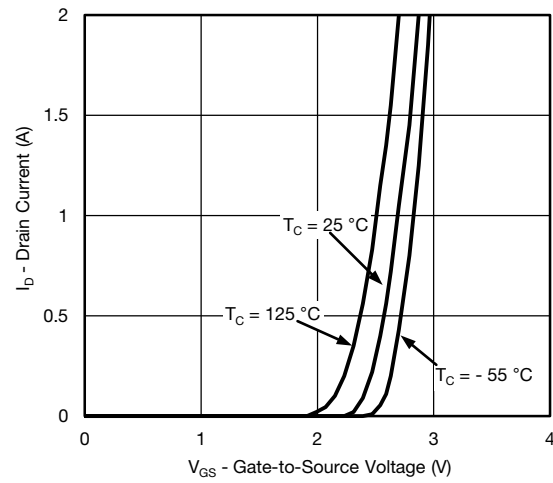
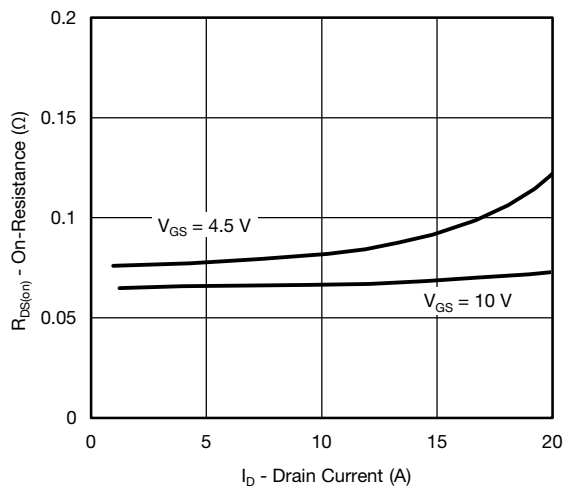
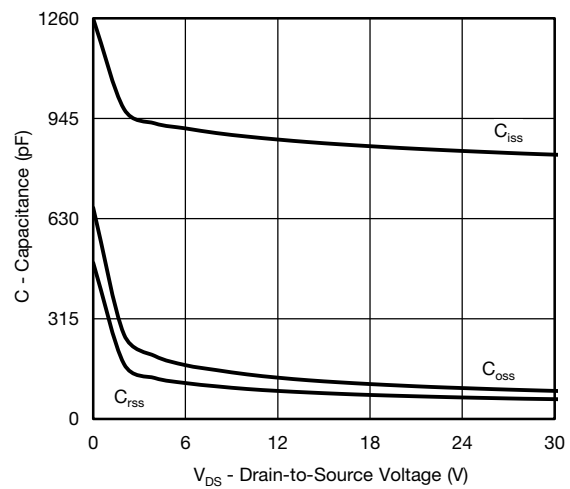
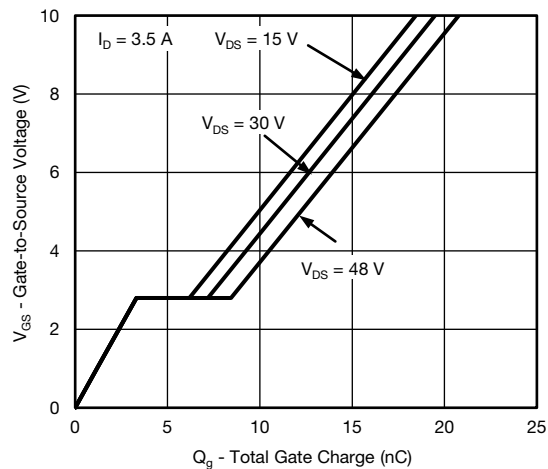
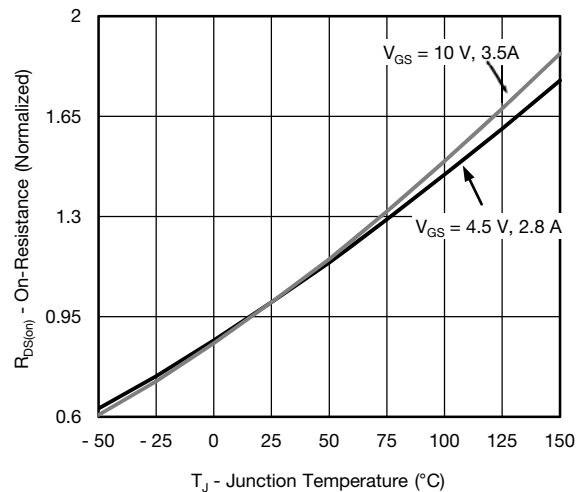
- Surface mounted on 1" x 1" FR4 board.
- $t = 10$ s.
- Maximum under steady state conditions is 110 °C/W.
- Based on $T_C = 25$ °C.

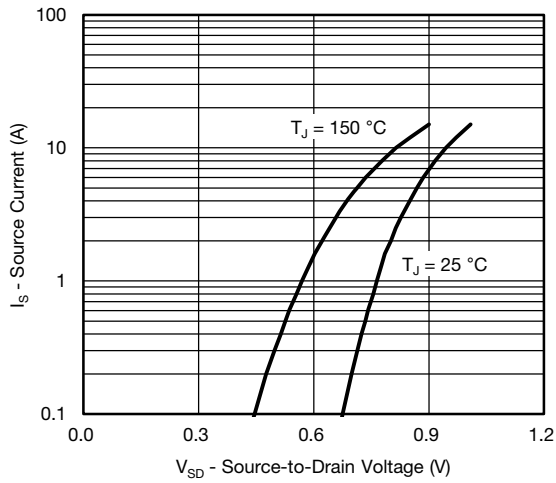
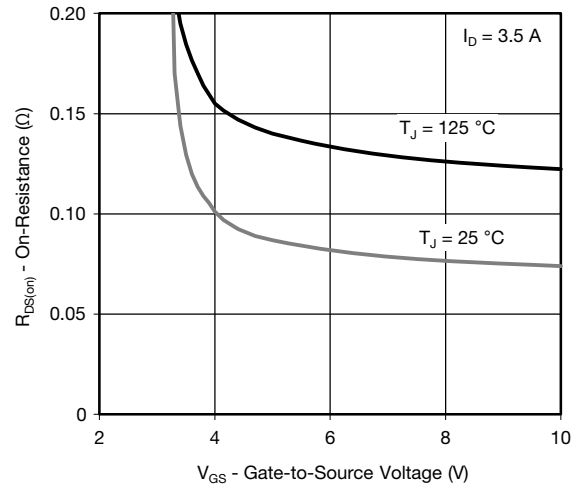
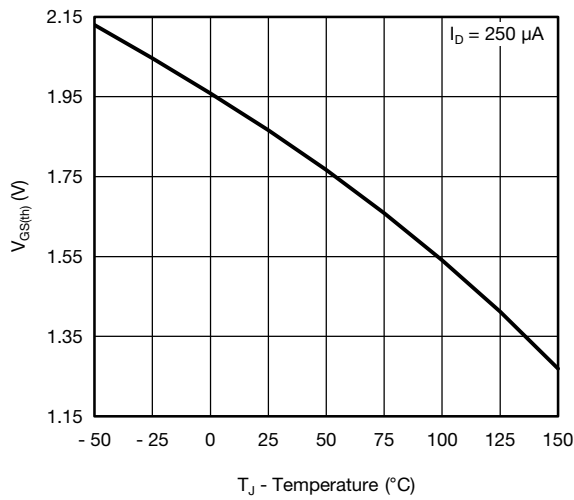
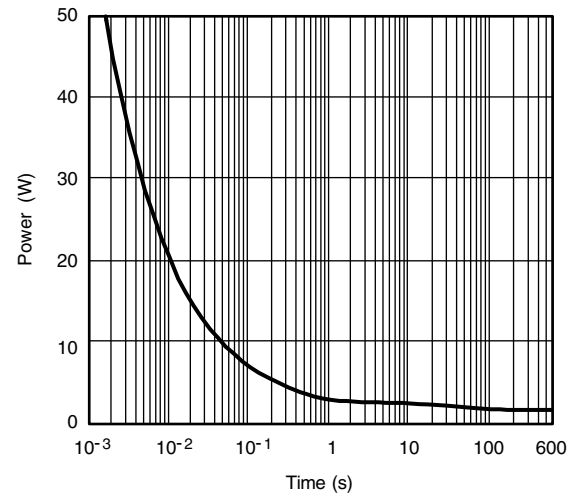
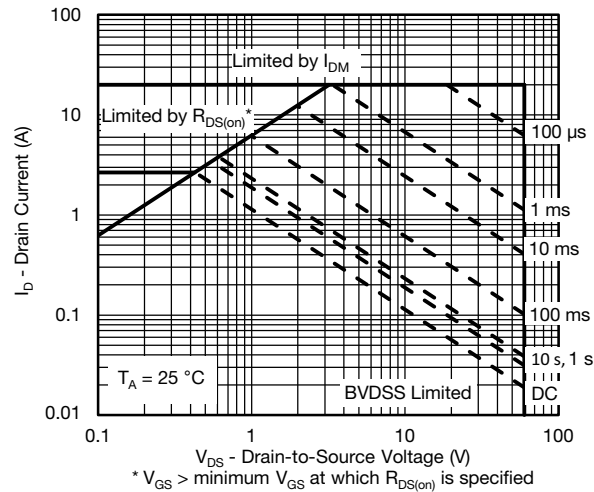
SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = -250 μA	-60	-	-	V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = -250 μA	-	-6.7	-	mV/°C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J		-	4.3	-	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250 μA	-1	-	-3	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V	-	-	± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -60 V, V _{GS} = 0 V	-	-	-1	μA
		V _{DS} = -60 V, V _{GS} = 0 V, T _J = 55 °C	-	-	-5	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ -10 V, V _{GS} = -10 V	-30	-	-	A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = -10 V, I _D = -3.5 A	-	0.070	-	Ω
		V _{GS} = -4.5 V, I _D = -2.8 A	-	0.085	-	
Forward Transconductance ^a	g _{fs}	V _{DS} = -30 V, I _D = -3.5 A	-	11	-	S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{DS} = -30 V, V _{GS} = 0 V, f = 1 MHz	-	832	-	pF
Output Capacitance	C _{oss}		-	88	-	
Reverse Transfer Capacitance	C _{rss}		-	63	-	
Total Gate Charge	Q _g	V _{DS} = -30 V, V _{GS} = -10 V, I _D = -3.5 A	-	20	30	nC
		V _{DS} = -30 V, V _{GS} = -4.5 V, I _D = -3.5 A	-	10.1	15.2	
Gate-Source Charge	Q _{gs}		-	3.3	-	
Gate-Drain Charge	Q _{gd}		-	3.9	-	
Gate Resistance	R _g	f = 1 MHz	1.8	9	18	Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = -30 V, R _L = 10.7 Ω I _D ≅ -2.8 A, V _{GEN} = -10 V, R _g = 1 Ω	-	8	16	ns
Rise Time	t _r		-	6	12	
Turn-Off DelayTime	t _{d(off)}		-	35	53	
Fall Time	t _f		-	16	24	
Turn-On Delay Time	t _{d(on)}	V _{DD} = -30 V, R _L = 10.7 Ω I _D ≅ -2.8 A, V _{GEN} = -4.5 V, R _g = 1 Ω	-	40	60	
Rise Time	t _r		-	28	42	
Turn-Off DelayTime	t _{d(off)}		-	31	47	
Fall Time	t _f		-	15	23	
Drain-Source Body Diode Characteristics						
Continous Source-Drain Diode Current	I _S	T _C = 25 °C	-	-	-3.5	A
Pulse Diode Forward Current (t = 100 μs)	I _{SM}		-	-	-20	
Body Diode Voltage	V _{SD}	I _S = -2.8 A, V _{GS} = 0 V	-	-0.85	-1.2	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = -2.8 A, dI/dt = 100 A/μs, T _J = 25 °C	-	32	48	ns
Body Diode Reverse Recovery Charge	Q _{rr}		-	45	68	nC
Reverse Recovery Fall Time	t _a		-	24	-	ns
Reverse Recovery Rise Time	t _b		-	8	-	

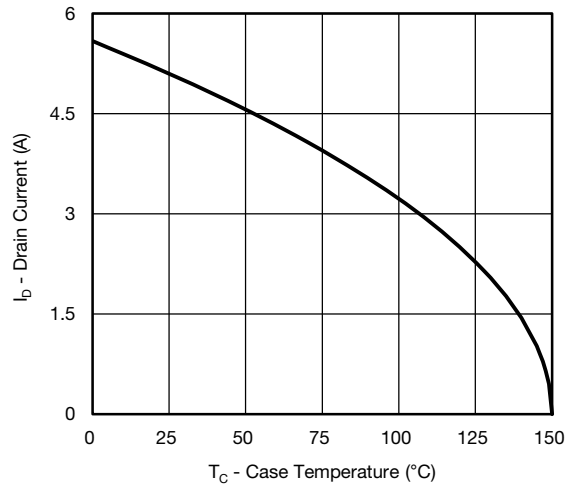
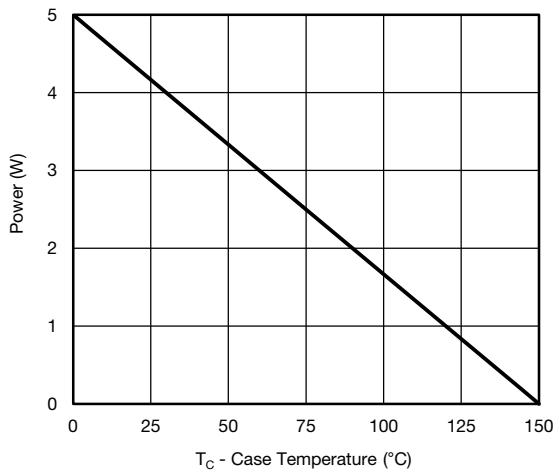
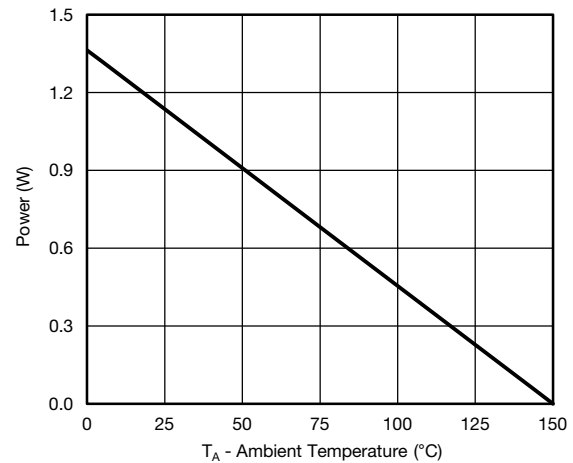
Notes

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 b. Guaranteed by design, not subject to production testing.

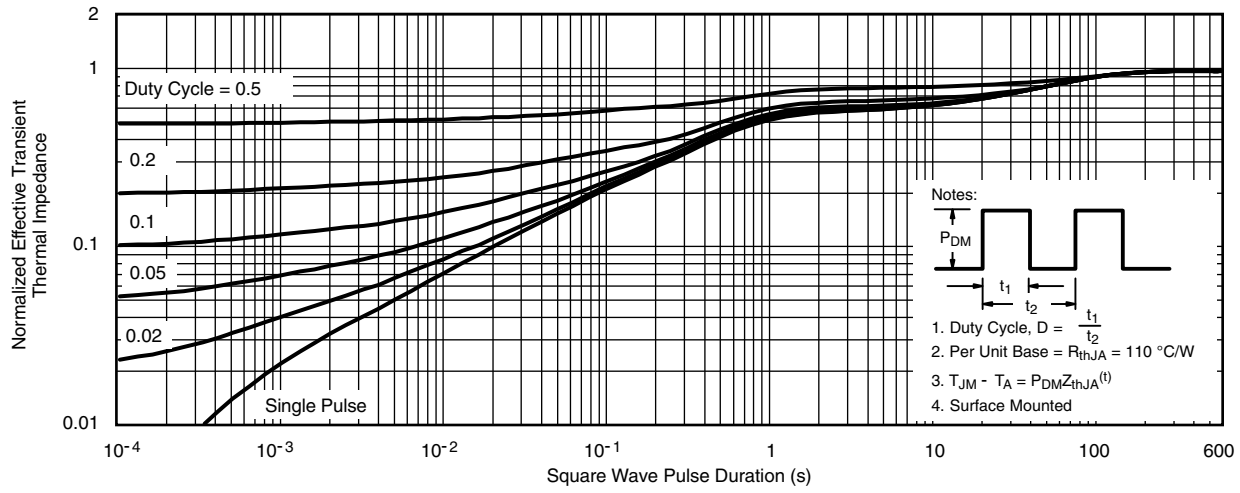
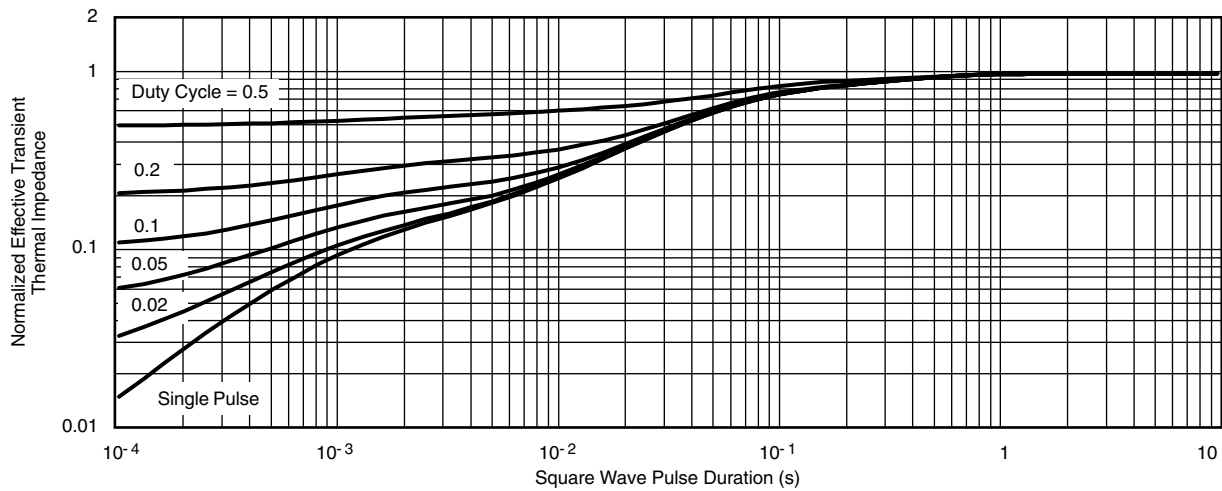
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Output Characteristics

Transfer Characteristics

On-Resistance vs. Drain Current

Capacitance

Gate Charge

On-Resistance vs. Junction Temperature

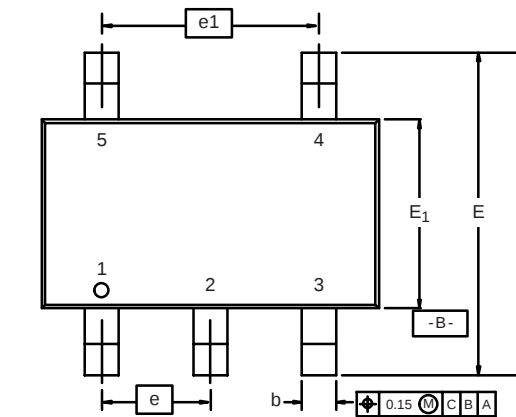
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Source-Drain Diode Forward Voltage

On-Resistance vs. Gate-to-Source Voltage

Threshold Voltage

Single Pulse Power, Junction-to-Ambient

Safe Operating Area

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Current Derating*

Power, Junction-to-Foot

Power Derating, Junction-to-Ambient

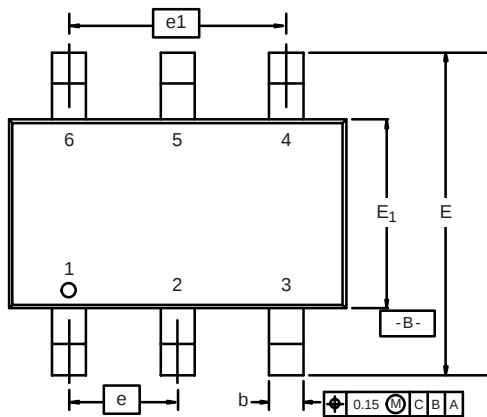
* The power dissipation P_D is based on $T_{J(max.)} = 150\text{ °C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Normalized Thermal Transient Impedance, Junction-to-Ambient

Normalized Thermal Transient Impedance, Junction-to-Foot

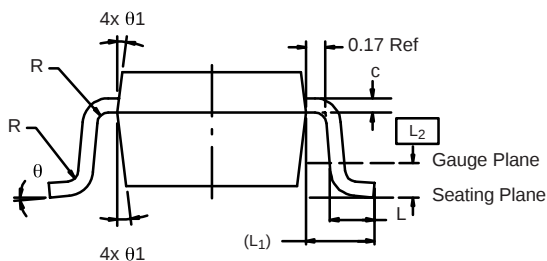
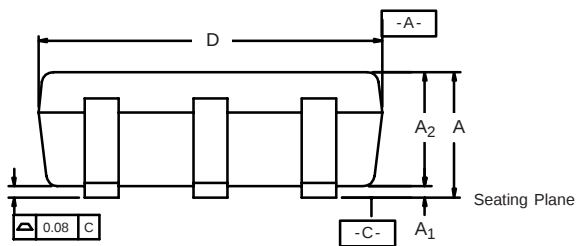
TSOP: 5/6-LEAD
JEDEC Part Number: MO-193C



5-LEAD TSOP

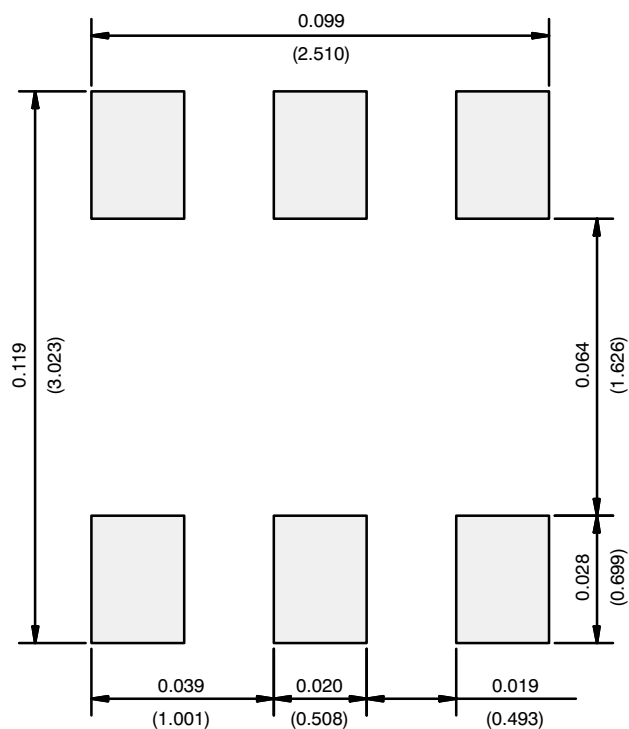


6-LEAD TSOP



	MILLIMETERS			INCHES		
Dim	Min	Nom	Max	Min	Nom	Max
A	0.91	-	1.10	0.036	-	0.043
A ₁	0.01	-	0.10	0.0004	-	0.004
A ₂	0.90	-	1.00	0.035	0.038	0.039
b	0.30	0.32	0.45	0.012	0.013	0.018
c	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
E	2.70	2.85	2.98	0.106	0.112	0.117
E ₁	1.55	1.65	1.70	0.061	0.065	0.067
e	0.95 BSC			0.0374 BSC		
e ₁	1.80	1.90	2.00	0.071	0.075	0.079
L	0.32	-	0.50	0.012	-	0.020
L ₁	0.60 Ref			0.024 Ref		
L ₂	0.25 BSC			0.010 BSC		
R	0.10	-	-	0.004	-	-
θ	0°	4°	8°	0°	4°	8°
θ ₁	7° Nom			7° Nom		
ECN: C-06593-Rev. I, 18-Dec-06						
DWG: 5540						

RECOMMENDED MINIMUM PADS FOR TSOP-6



Recommended Minimum Pads
Dimensions in Inches/(mm)

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